Fig. 1 (Prior Art)

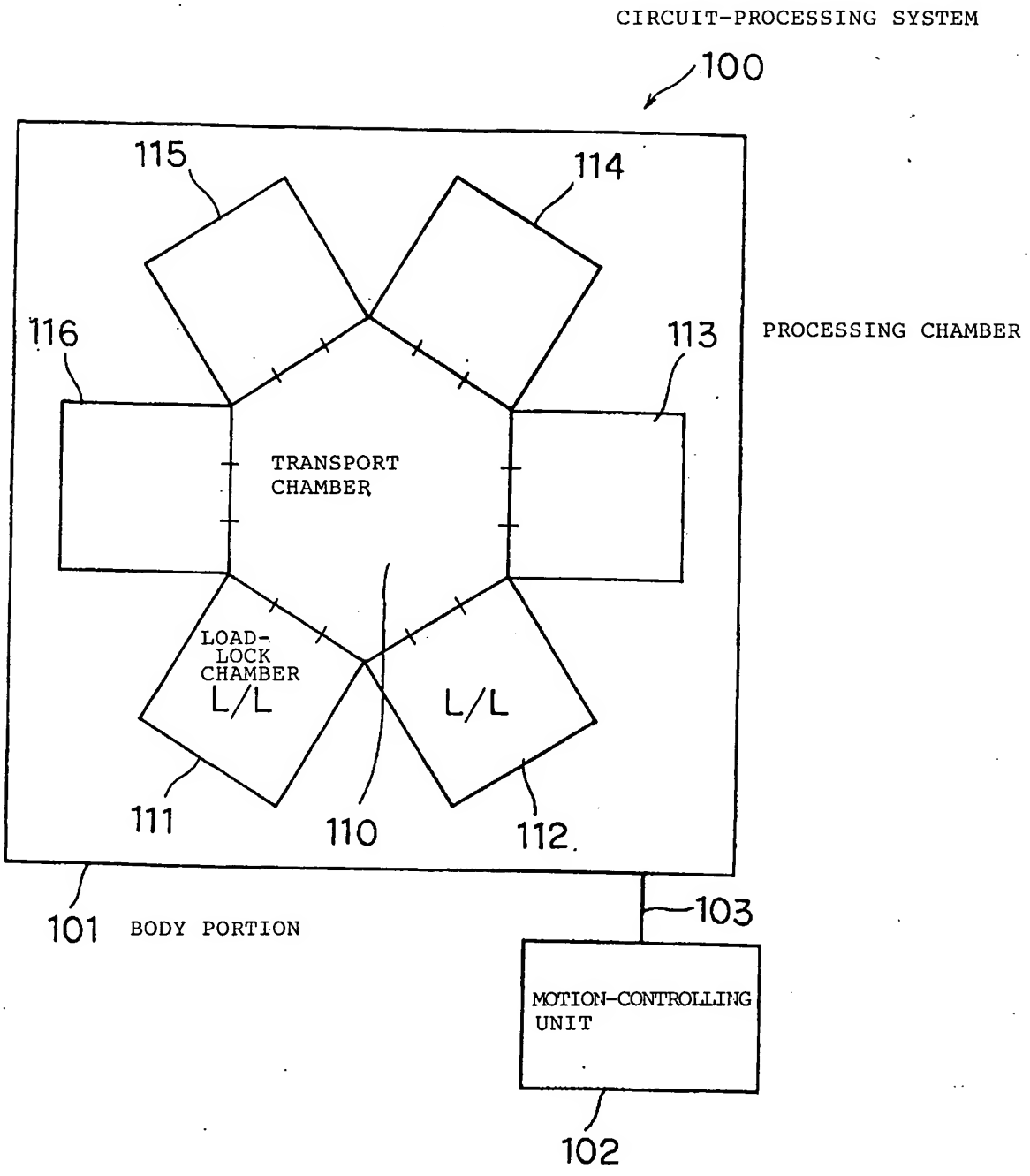


Fig. 2 (Prior Art)

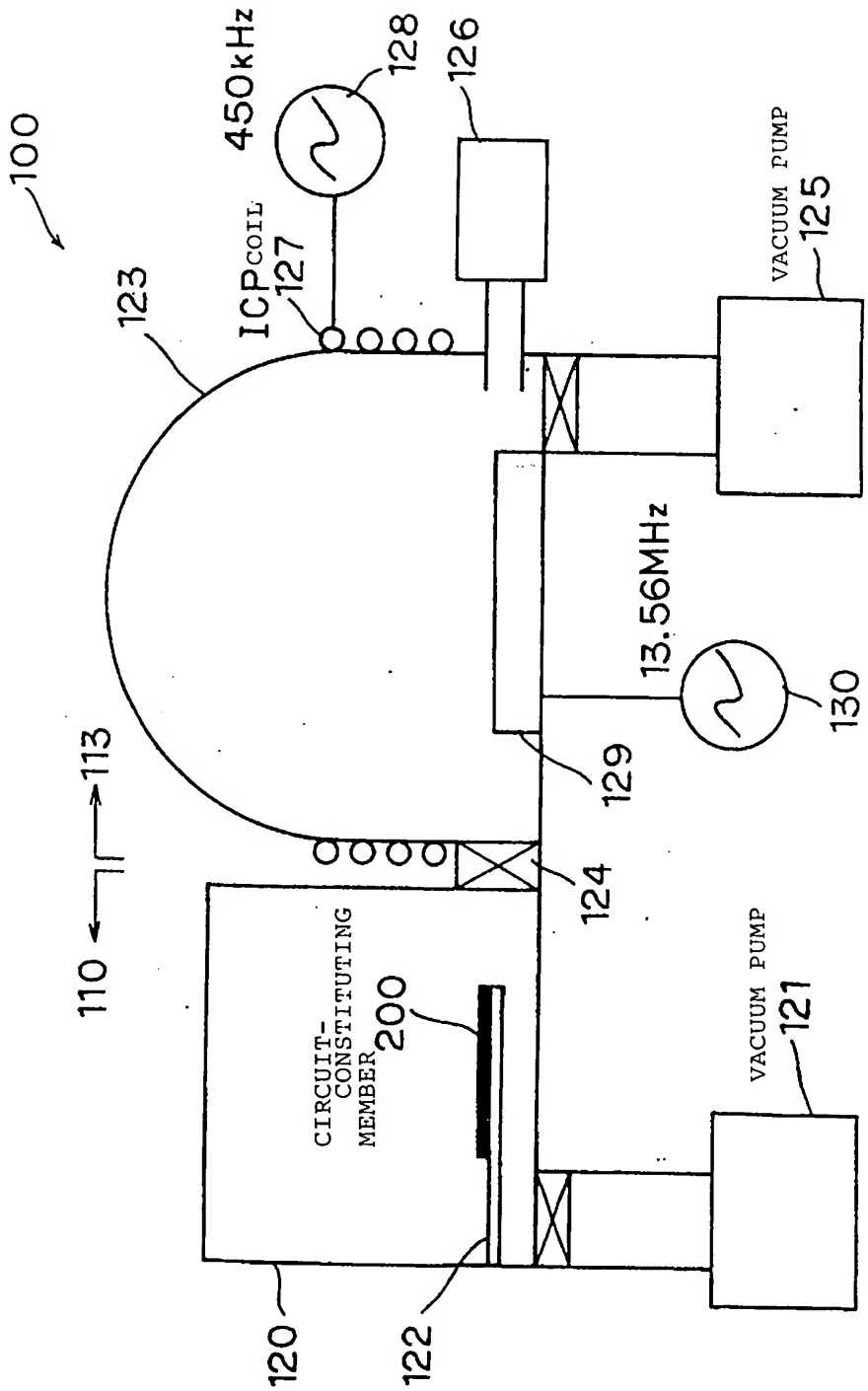
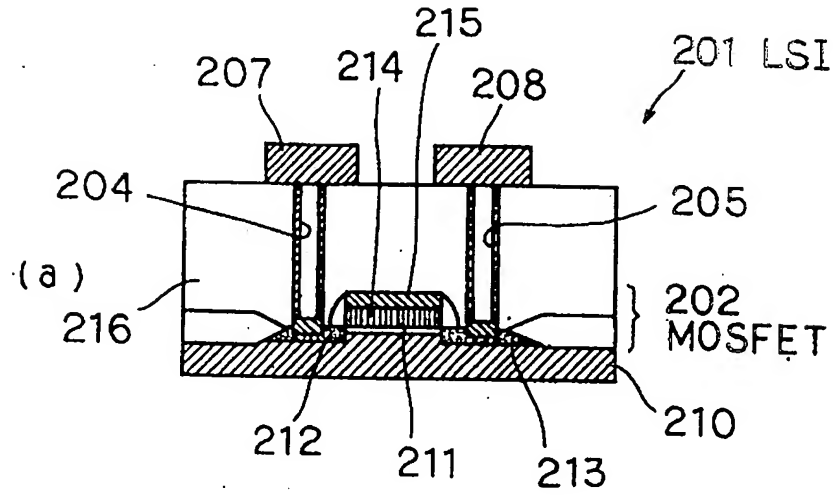


Fig. 3 (Prior Art)



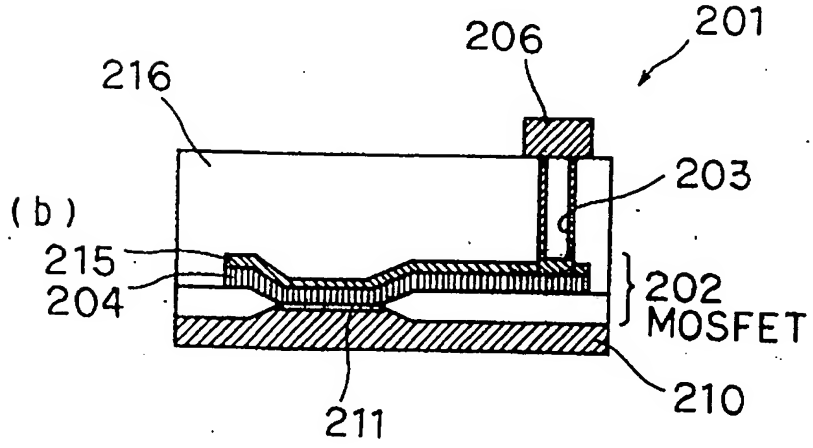


Fig. 4 (Prior Art)

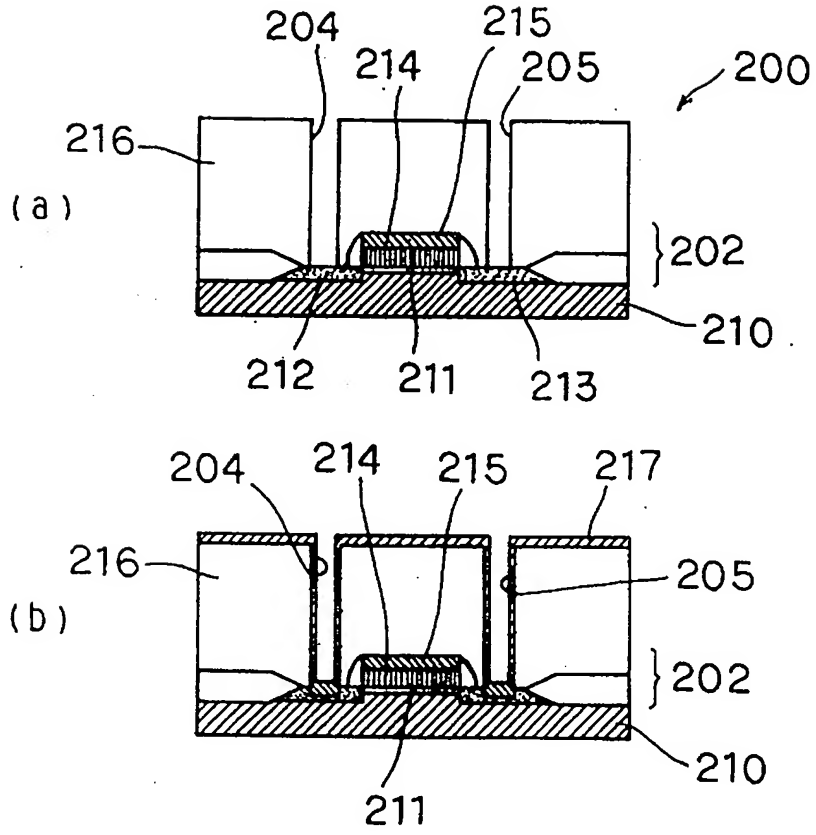


Fig. 5 (Prior Art)

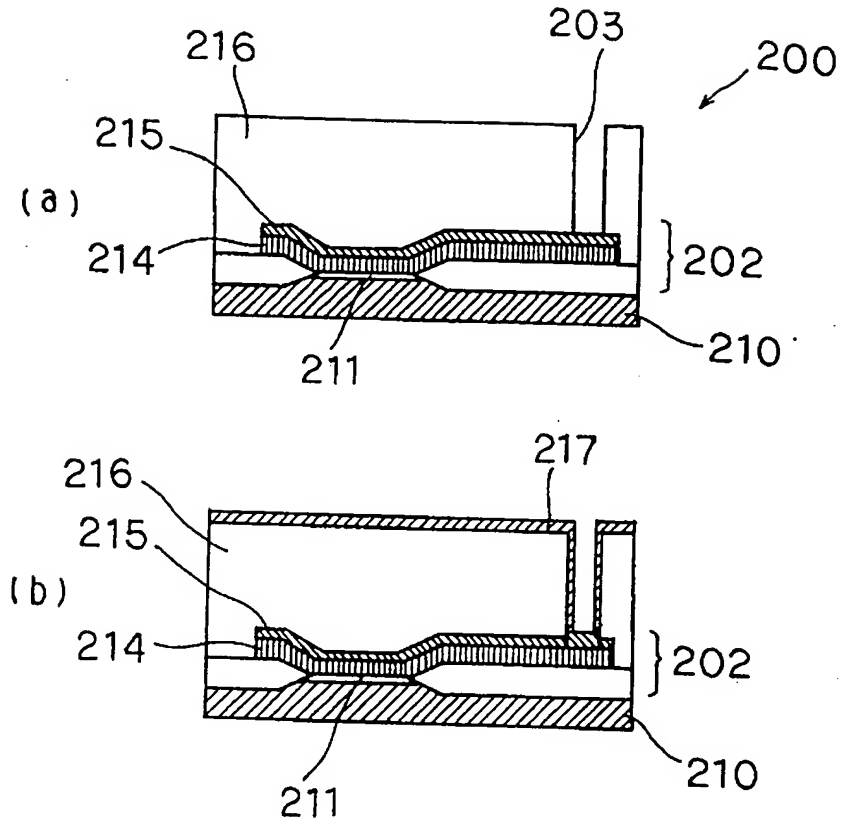


Fig. 6 (Prior Art)

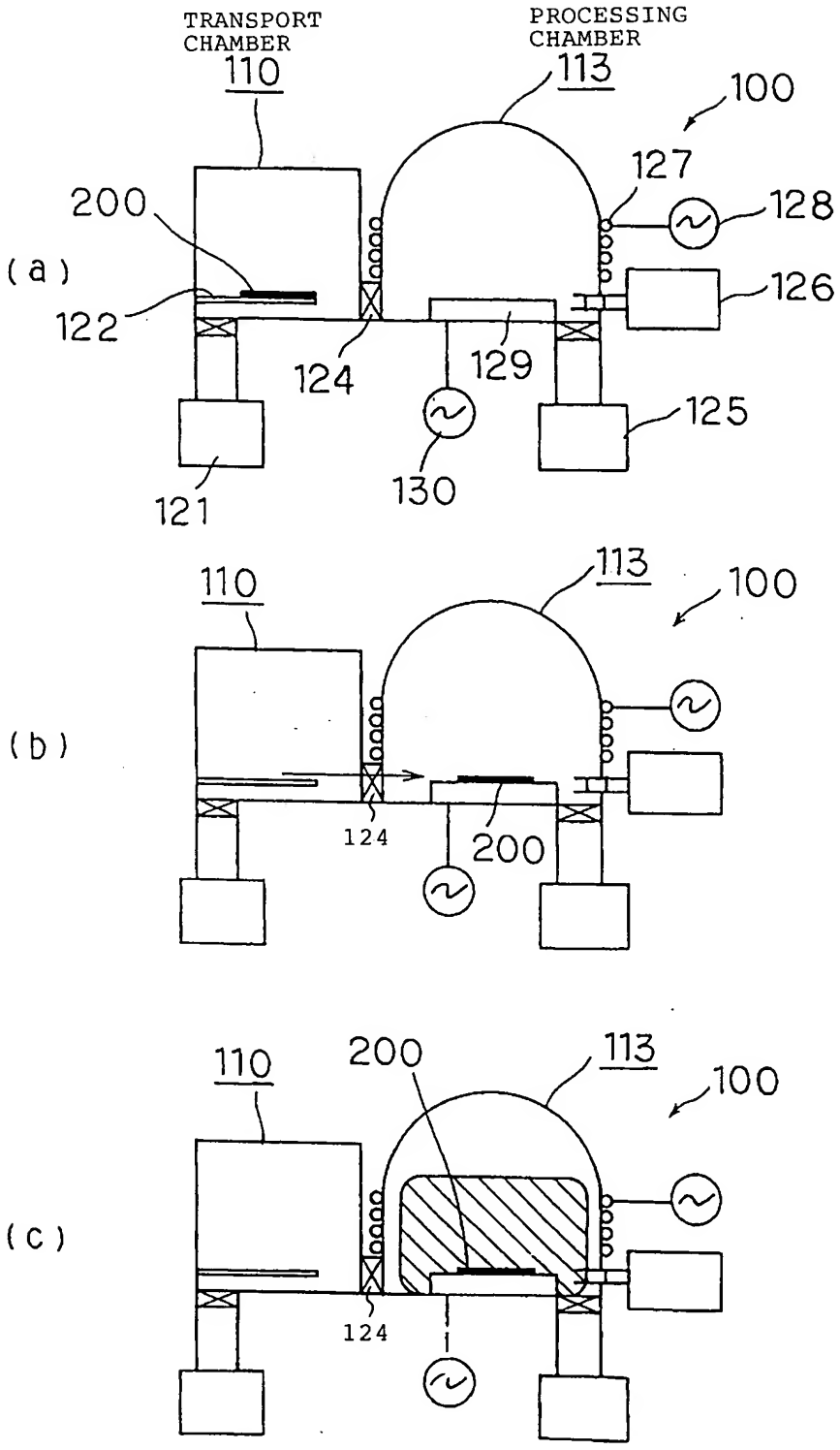


Fig. 7 (Prior Art)

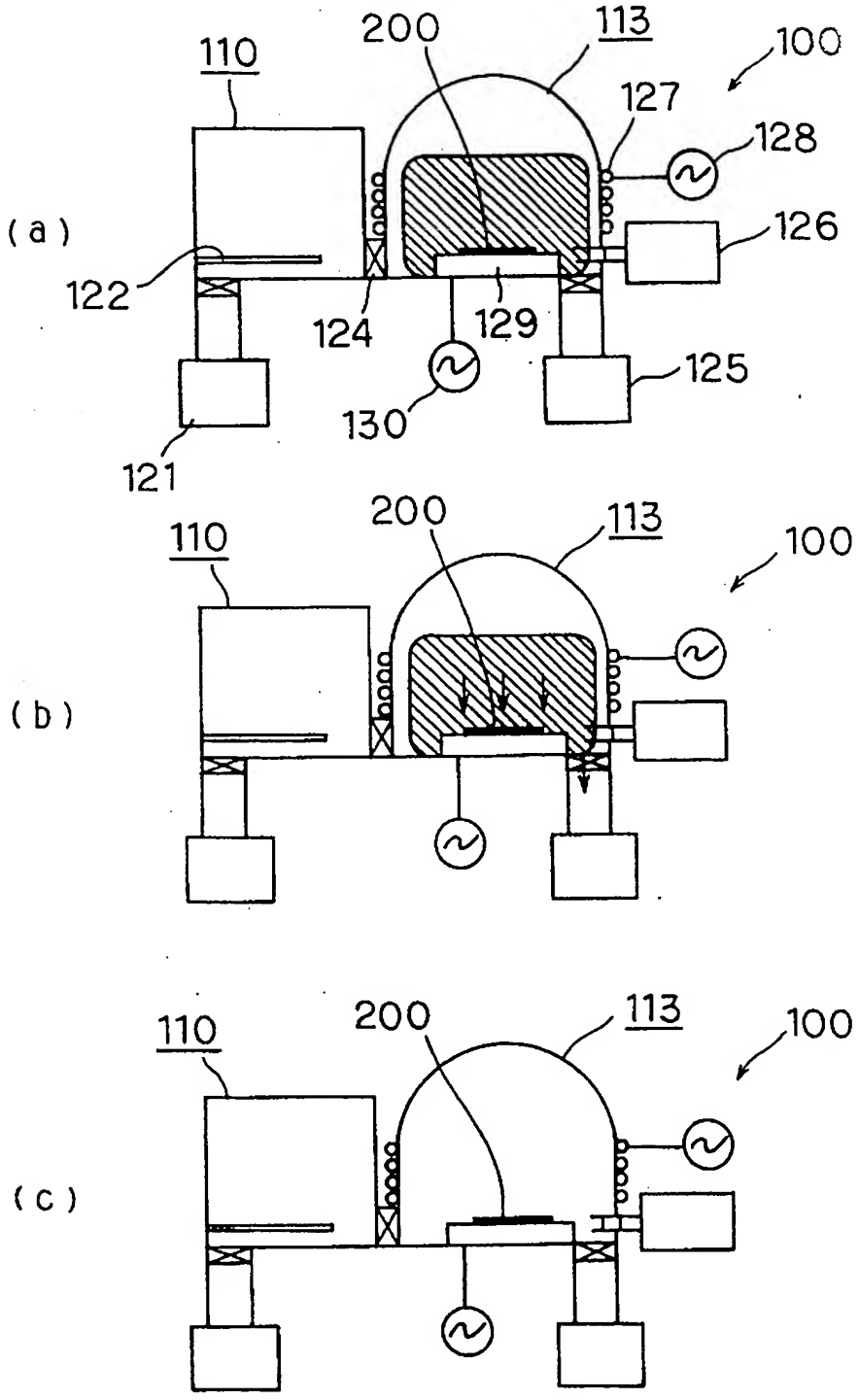


Fig. 8 (Prior Art)

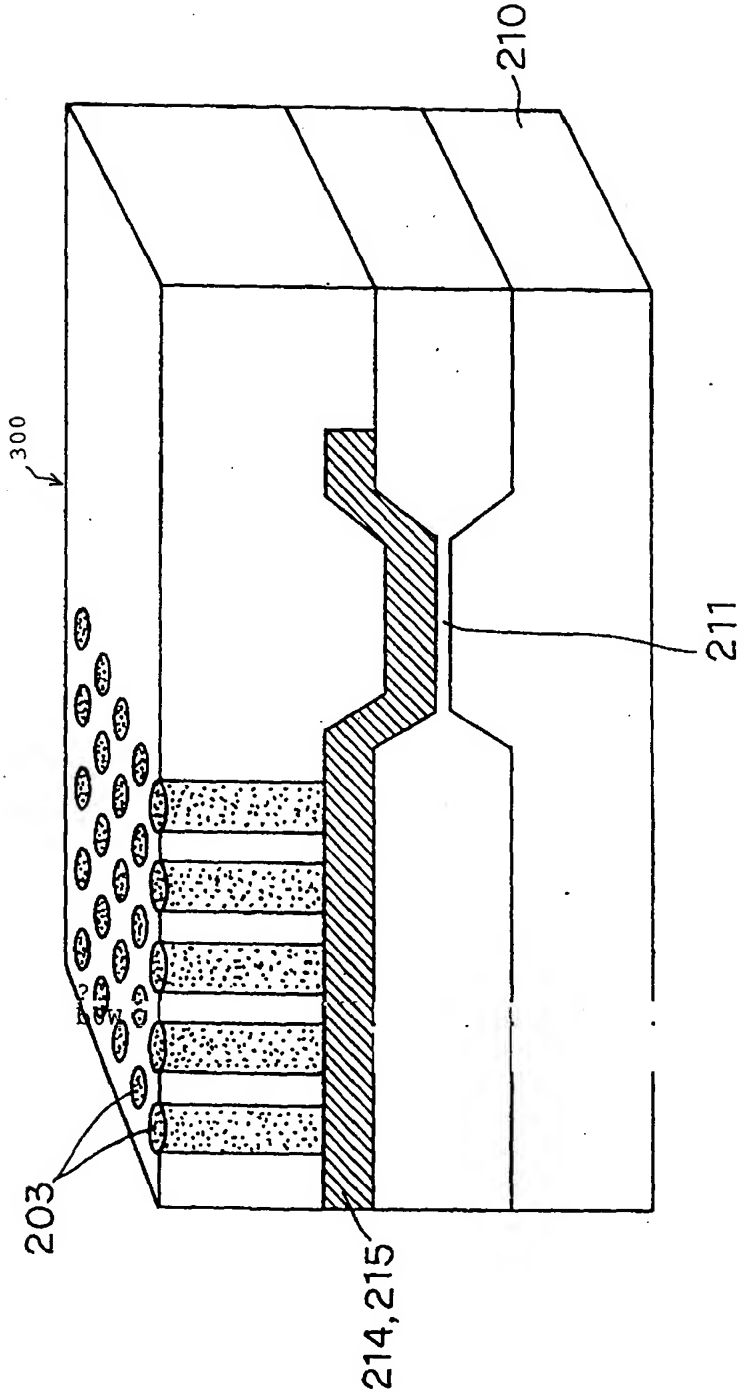


Fig. 9 (Prior Art)

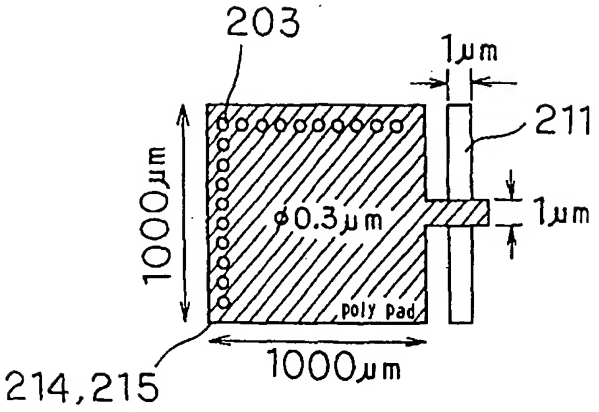


Fig. 10 (Prior Art)

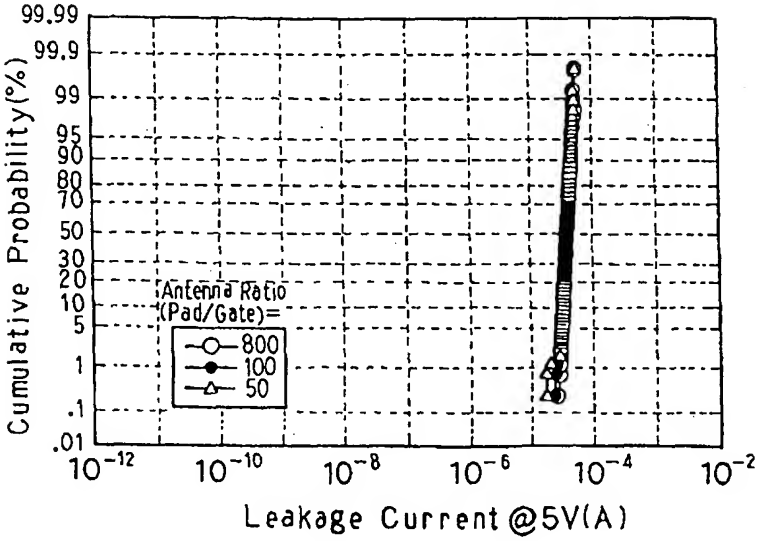


Fig. 11

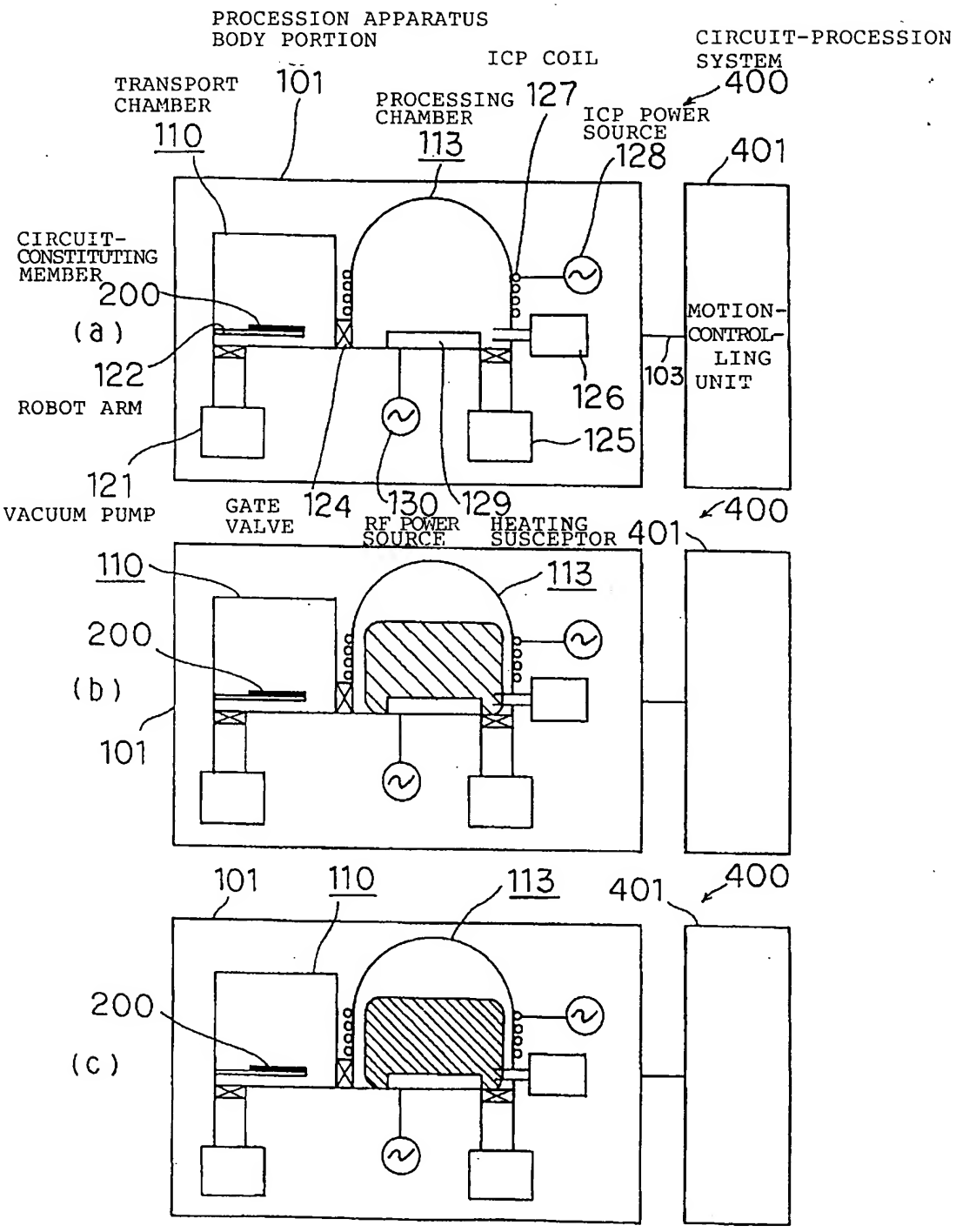

PROCESSION APPARATUS BODY PORTION
ICP COIL
CIRCUIT-PROCESSION SYSTEM
400
TRANSPORT CHAMBER
101
PROCESSING CHAMBER
127
ICP POWER SOURCE
110
113
128
401
CIRCUIT-CONSTITUTING MEMBER
200
(a)
122
ROBOT ARM
121
VACUUM PUMP
GATE VALVE
124
130
RF POWER SOURCE
129
HEATING SUSCEPTOR
126
125
103
MOTION-CONTROL-LING UNIT
(b)
(c)

Fig. 12

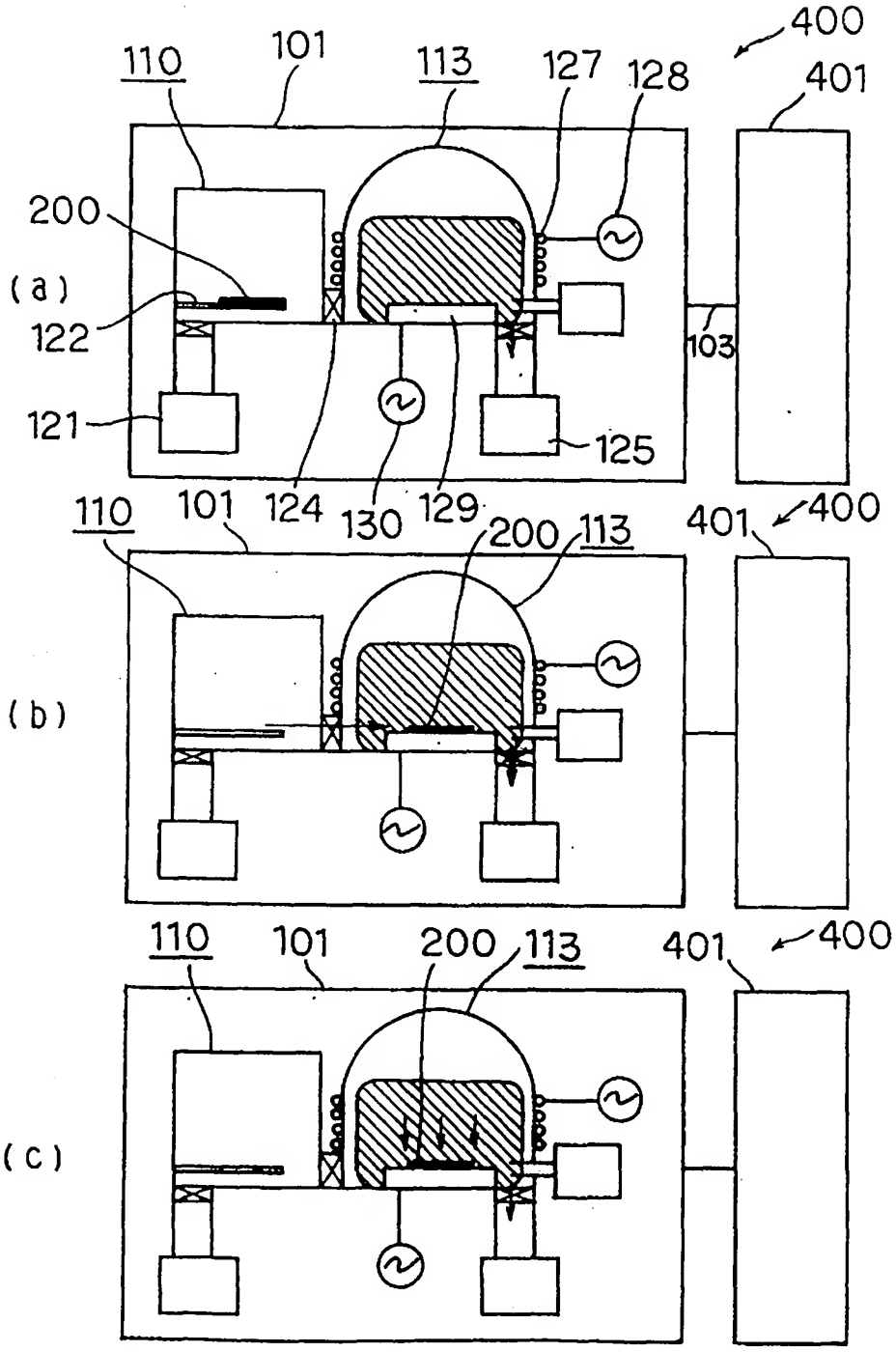

400
110
101
113
127
128
401
200
(a)
122
103
121
125
124
130
129
110
101
200
113
401
400
(b)
110
101
200
113
401
400
(c)

Fig. 13

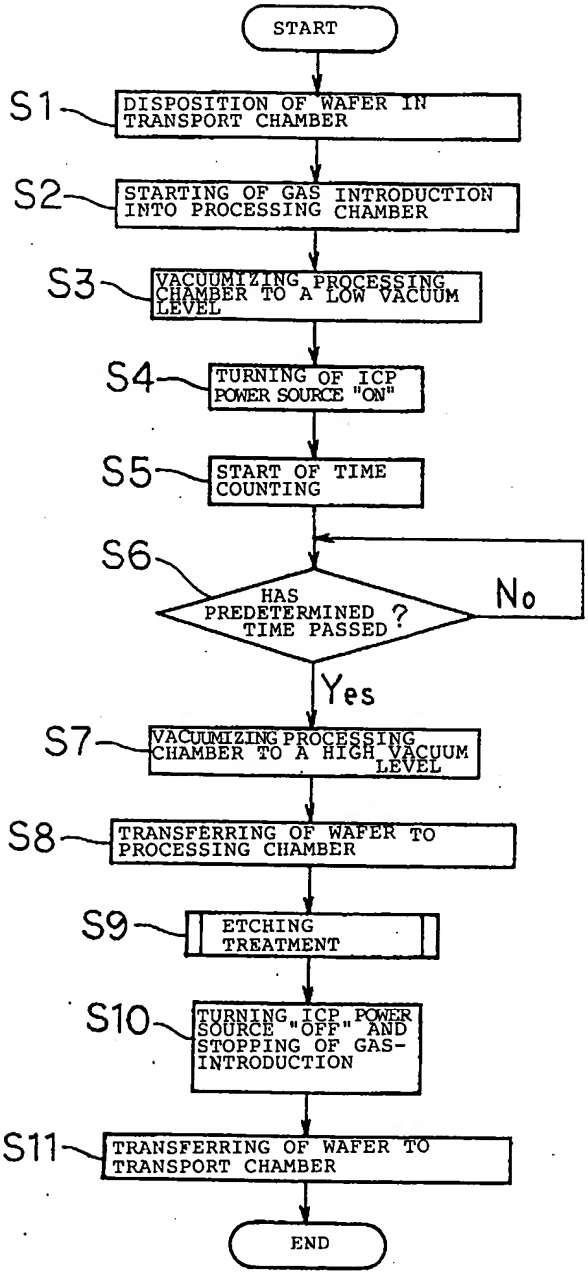
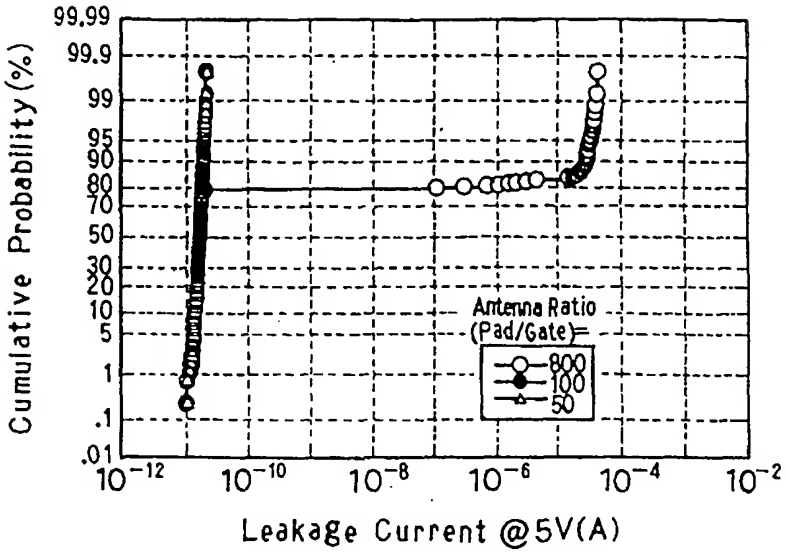

START
S1
DISPOSITION OF WAFER IN TRANSPORT CHAMBER
S2
STARTING OF GAS INTRODUCTION INTO PROCESSING CHAMBER
S3
VACUUMIZING PROCESSING CHAMBER TO A LOW VACUUM LEVEL
S4
TURNING OF ICP POWER SOURCE "ON"
S5
START OF TIME COUNTING
S6
HAS PREDETERMINED TIME PASSED ?
No
Yes
S7
VACUUMIZING PROCESSING CHAMBER TO A HIGH VACUUM LEVEL
S8
TRANSFERRING OF WAFER TO PROCESSING CHAMBER
S9
ETCHING TREATMENT
S10
TURNING ICP POWER SOURCE "OFF" AND STOPPING OF GAS-INTRODUCTION
S11
TRANSFERRING OF WAFER TO TRANSPORT CHAMBER
END

Fig. 14


Cumulative Probability (%)
99.99
99.9
99
95
90
80
70
50
30
20
10
5
1
.1
.01
10^{-12}
10^{-10}
10^{-8}
10^{-6}
10^{-4}
10^{-2}
Leakage Current @5V(A)
Antenna Ratio
(Pad/Gate)=
800
100
50